

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

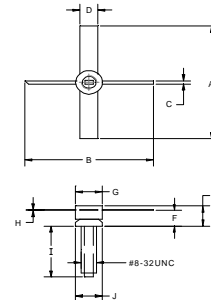
The **ASI TVU0.5B** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CB0}	45 V
V_{CEO}	25 V
V_{EBO}	3.5 V
P_{DISS}	31.8 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	33 °C/W

PACKAGE STYLE .205 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.000 / 25.4000
B	.976 / 24.800	1.000 / 25.4000
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.161 / 4.100	.196 / 5.000
F	.098 / 2.500	.110 / 2.800
G	.200 / 5.100	.208 / 5.300
H	.004 / 0.100	.006 / 0.150
I	.425 / 10.800	.465 / 11.800
J	.200 / 5.100	2.05 / 5.200

ORDER CODE: ASI10642
CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 1.0 mA	45			V
BV_{CE}	I _C = 20 mA	24			V
BV_{EBO}	I _E = 0.25 mA	3.5			V
I_{CB0}	V _{CB} = 28 V			0.45	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	15		120	---
P_G	V _{CE} = 20 V I _C = 150 mA f = 860 MHz	12			dB
IMD₁	P _{OUT} = 0.5 W	-58			dBc